(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
6 November 2008 (06.11.2008)

PCT

(10) International Publication Number
WO 2008/133832 A1

(51) International Patent Classification:
H01L 29/78 (2006.01) *H01L 29/417* (2006.01)
H01L 21/8238 (2006.01) *H01L 23/528* (2006.01)
H01L 21/336 (2006.01)

(21) International Application Number:
PCT/US2008/004958

(22) International Filing Date: 17 April 2008 (17.04.2008)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10 2007 020 258.1 30 April 2007 (30.04.2007) DE
11/964,494 26 December 2007 (26.12.2007) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL,

[Continued on next page]

(54) Title: A TECHNIQUE FOR ENHANCING TRANSISTOR PERFORMANCE BY TRANSISTOR SPECIFIC CONTACT DESIGN

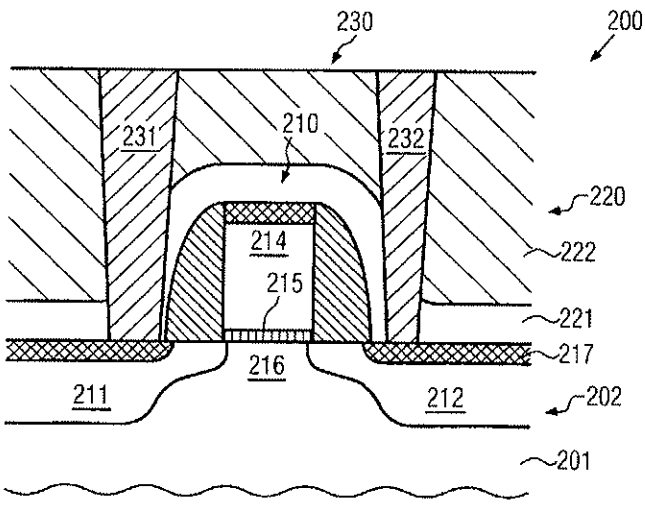


FIG. 2b

(57) Abstract: By locally adapting the size and/or density of a contact structure (230A, 230B), for instance, within individual transistors (210, 210A, 210B) or in a more global manner, the overall performance of advanced semiconductor devices (200) may be increased. Hence, the mutual interaction between the contact structure (230A, 230B) and local device characteristics may be taken into consideration. On the other hand, a high degree of compatibility with conventional process strategies may be maintained.

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